

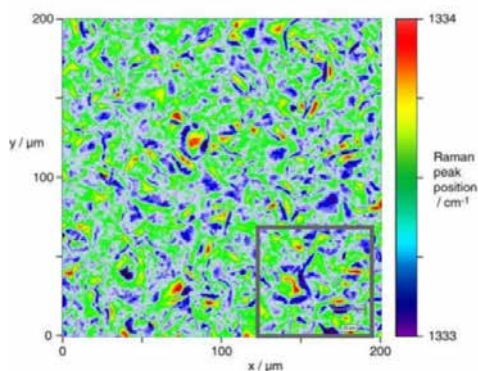


Raman microscope with three
laser sources

Confocal Raman microscope

Fields of application

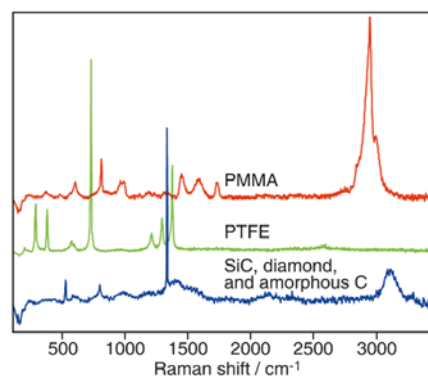
- Non-destructive local optical analysis of
 - MOEMS chips
 - Wafers
 - devices
 - other samples
- Microscopic, spectral material characterization in the range of 100 cm^{-1} to 4200 cm^{-1}



Raman mapping with 100 nm positioning
accuracy

Measurement services

- Characterization of crystallographic properties
 - Lattice structures
 - Crystallinity
 - Interfaces
- Mechanical stress analysis
- Determination of composition and contamination



Raman spectra of plastics and semiconductor
materials

Part of



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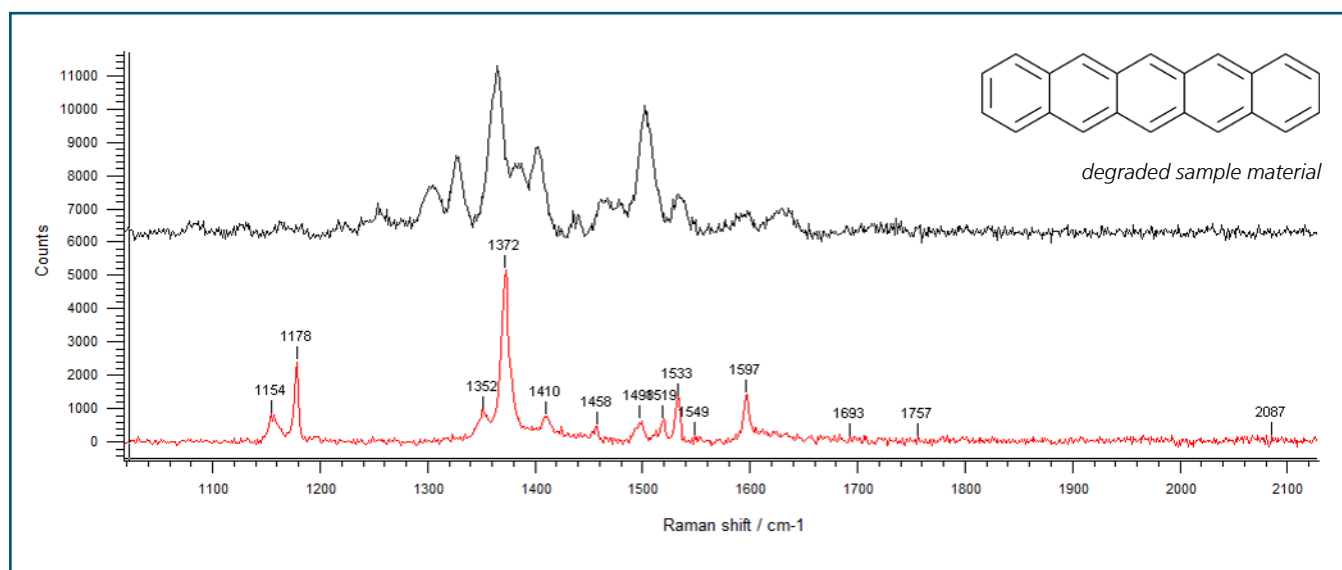
Temperature independent measurements
from -196 °C up to 1400 °C



Analysis of a 200 mm Si wafer
with 100 nm positioning accuracy

Specifications

Spectrometer	spectral resolution (FWHM)	1.0 cm ⁻¹ / < 0.33 cm ⁻¹ /pixel
	spectral repeatability	< +/- 0.01 cm ⁻¹ (1σ)
	spectral stability (within 7 hours)	< +/- 0.05 cm ⁻¹ (1σ)
	cut-off wavenumber (low)	100 cm ⁻¹
	cut-off wavenumber (low) - optional	< 50 cm ⁻¹
	cut-off wavenumber (high)	< 4200 cm ⁻¹
Laser kit	405 nm, 532 nm, 785 nm	> 45 mW (cw)
Microscope	Leica DM2700	NPLAN lens: 5x/NA0.12; 20x/NA0.4; 50x/NA0.5; 100x/NA0.85
Sample holder	X/Y/Z motorized high-speed coding	200 mm x 200 mm sample size 100 nm positioning accuracy
Heating/cooling	active sample heating/cooling	-196 °C - 1400 °C



Material analysis of organic molecules before and after aging using pentacene as an example